Features

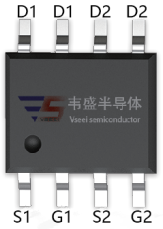
- Low Gate Charge
- 100% UIS Tested, 100% R_g Tested
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant

Applications

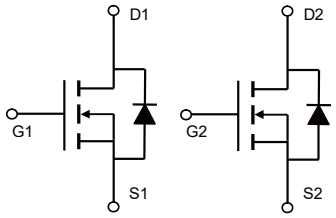
- Power Managerment in Telecom., Industrial Automation, CE
- Current Switching in DC/DC & AC/DC Sub-systems

Product Summary

Parameter	Value	Unit
V_{DS}	100	V
$V_{GS(th)_Typ}$	1.7	V
I_D (@ V_{GS} = 10V) (1)	2.4	A
$R_{DS(ON)_Typ}$ (@ V_{GS} = 10V)	111	mΩ
$R_{DS(ON)_Typ}$ (@ V_{GS} = 4.5V)	155	mΩ



SOP-8



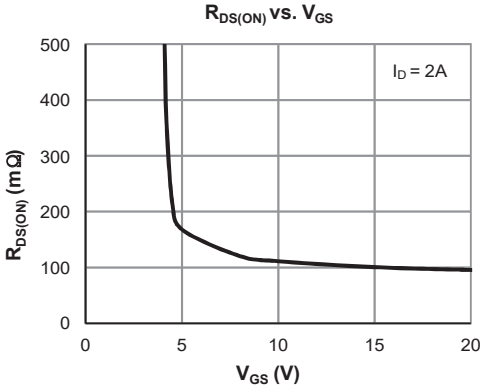
Schematic

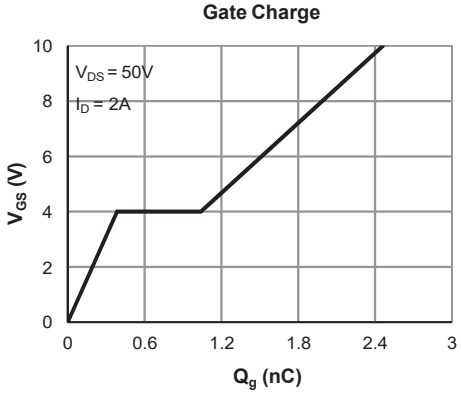
Ordering Information

Device	Package	# of Pins	Marking	MSL	T_J (°C)	Media	Quantity (pcs)
VSM2DN10-S8	SOP-8	8	VSM2DN10	3	-55 to 150	13-inch Reel	2500

Absolute Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V_{DS}	100	V
Gate-to-Source Voltage		V_{GS}	±20	V
Continuous Drain Current (1)	T_A = 25°C	I_D	2.4	A
	T_A = 70°C		1.9	
Pulsed Drain Current (2)		I_{DM}	9.5	A
Avalanche Current (3)		I_{AS}	4.3	A
Avalanche Energy (3)		E_{AS}	0.92	mJ
Power Dissipation (4)	T_A = 25°C	P_D	2.5	W
	T_A = 70°C		1.6	
Junction & Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C





Electrical Characteristics (@ T_J = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D = 250 μA, V_{GS} = 0V	100			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 80V, V_{GS} = 0V			1.0	μA
		T_J = 55°C			5.0	
Gate-Body Leakage Current	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA	1.2	1.7	2.5	V
Static Drain-Source ON-Resistance	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 2A		111	139	mΩ
	$R_{DS(ON)}$	V_{GS} = 4.5V, I_D = 1A		155	195	mΩ
Forward Transconductance	g_{FS}	V_{DS} = 5V, I_D = 2A		4.5		S
Diode Forward Voltage	V_{SD}	I_S = 1A, V_{GS} = 0V		0.70	1.0	V
Diode Continuous Current	I_S	T_A = 25°C			2.5	A
DYNAMIC PARAMETERS (5)						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 50V, f = 1MHz		103		pF
Output Capacitance	C_{oss}			47		pF
Reverse Transfer Capacitance	C_{rss}			4.9		pF
Gate Resistance	R_g	V_{GS} = 0V, V_{DS}= 0V, f = 1MHz		2.6		Ω
SWITCHING PARAMETERS (5)						
Total Gate Charge (@ V_{GS} = 10V)	Q_g	V_{GS} = 0 to 10V, V_{DS} = 50V, I_D = 2A		2.5		nC
Total Gate Charge (@ V_{GS} = 4.5V)	Q_g			1.3		nC
Gate Source Charge	Q_{gs}			0.30		nC
Gate Drain Charge	Q_{gd}			0.70		nC
Turn-On DelayTime	$t_{D(on)}$	V_{GS} = 10V, V_{DS} = 50V, R_L = 25Ω, R_{GEN} = 6Ω		2.1		ns
Turn-On Rise Time	t_r			3.3		ns
Turn-Off DelayTime	$t_{D(off)}$			7.5		ns
Turn-Off Fall Time	t_f			3.2		ns
Body Diode Reverse Recovery Time	t_{rr}	I_F = 2A, dI_F/dt = 100A/μs		21		ns
Body Diode Reverse Recovery Charge	Q_{rr}	I_F = 2A, dI_F/dt = 100A/μs		8.0		nC

Thermal Performance

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient (t≤10s)	$R_{\theta JA}$	40	50	°C/W
Thermal Resistance, Junction-to-Ambient (steady state)	$R_{\theta JA}$	70	85	°C/W

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under T_{J_Max} = 150°C.
3. This single-pulse measurement was taken under the following condition [L = 100 μH, V_{GS} = 10V, V_{DS} = 50V] while its value is limited by T_{J_Max} = 150°C.
4. The power dissipation P_D is based on T_{J_Max} = 150°C.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Electrical & Thermal Characteristics

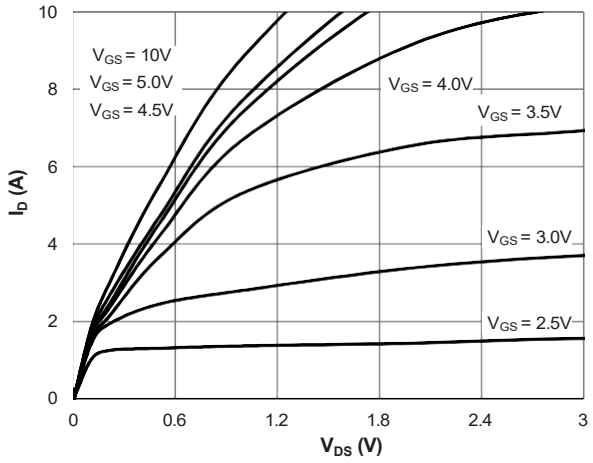


Figure 1: Saturation Characteristics

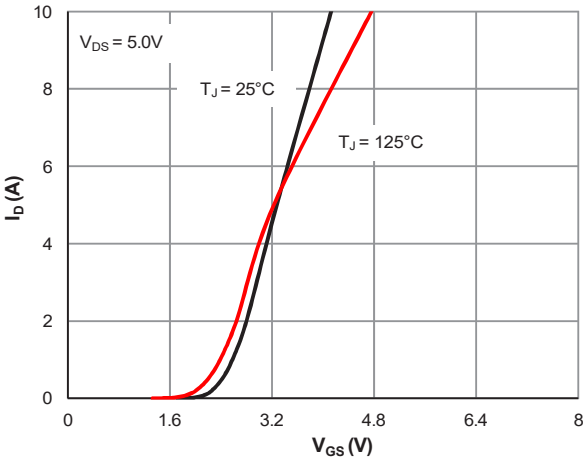


Figure 2: Transfer Characteristics

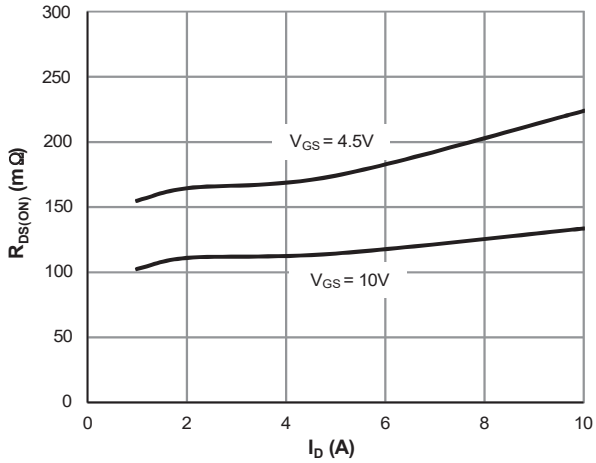


Figure 3: $R_{DS(ON)}$ vs. Drain Current

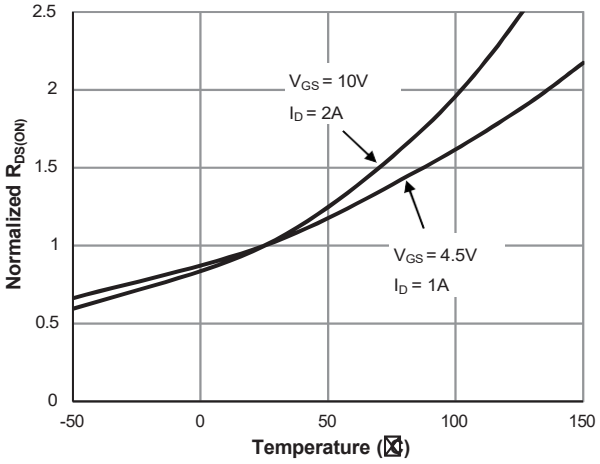


Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

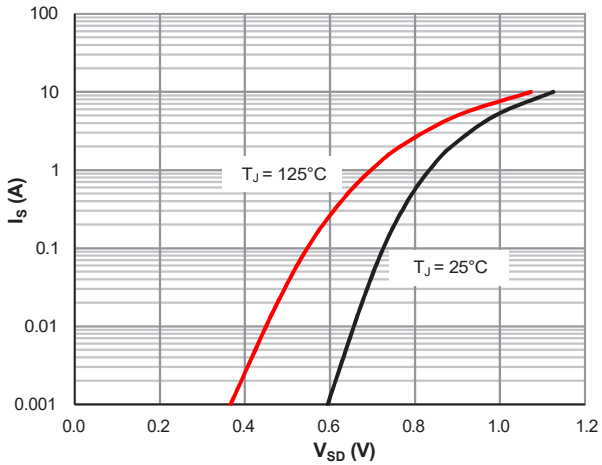


Figure 5: Body-Diode Characteristics

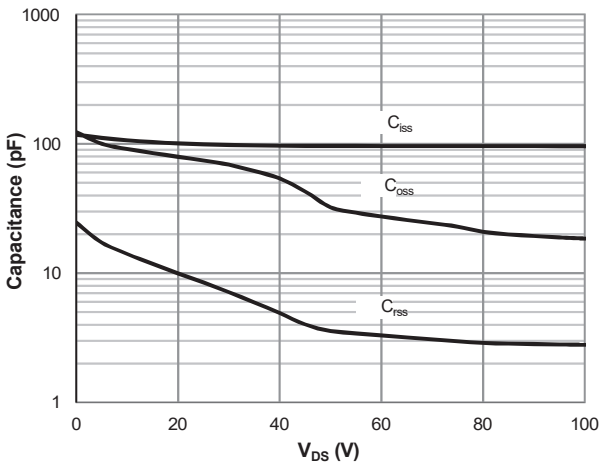


Figure 6: Capacitance Characteristics

Typical Electrical & Thermal Characteristics

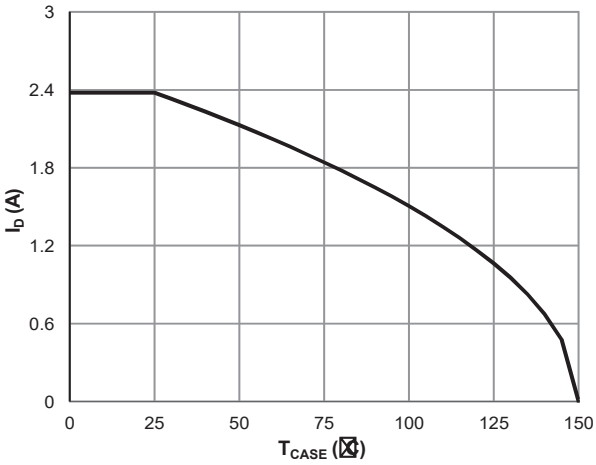


Figure 7: Current De-rating

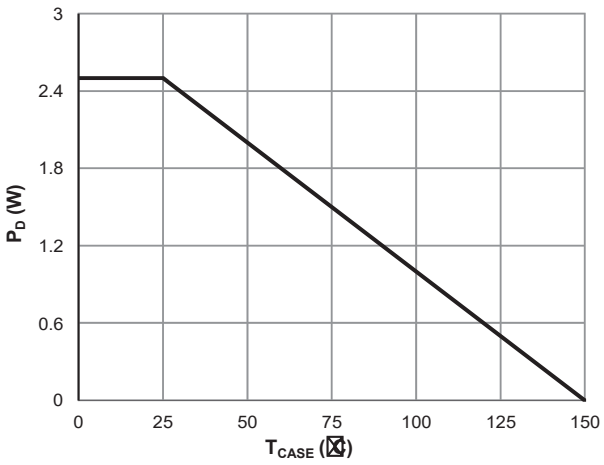


Figure 8: Power De-rating

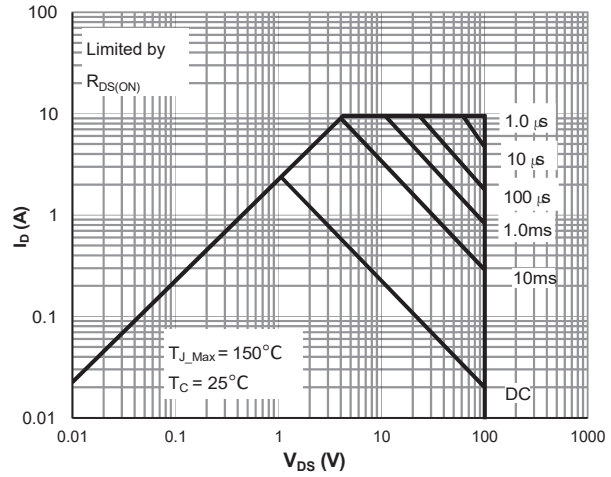


Figure 9: Maximum Safe Operating Area

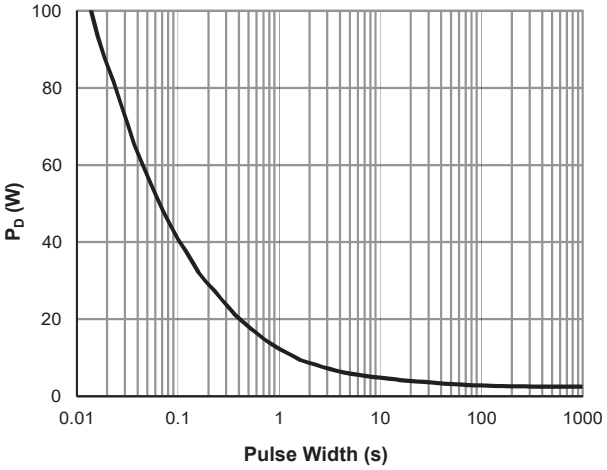


Figure 10: Single Pulse Power Rating, Junction-to-Case

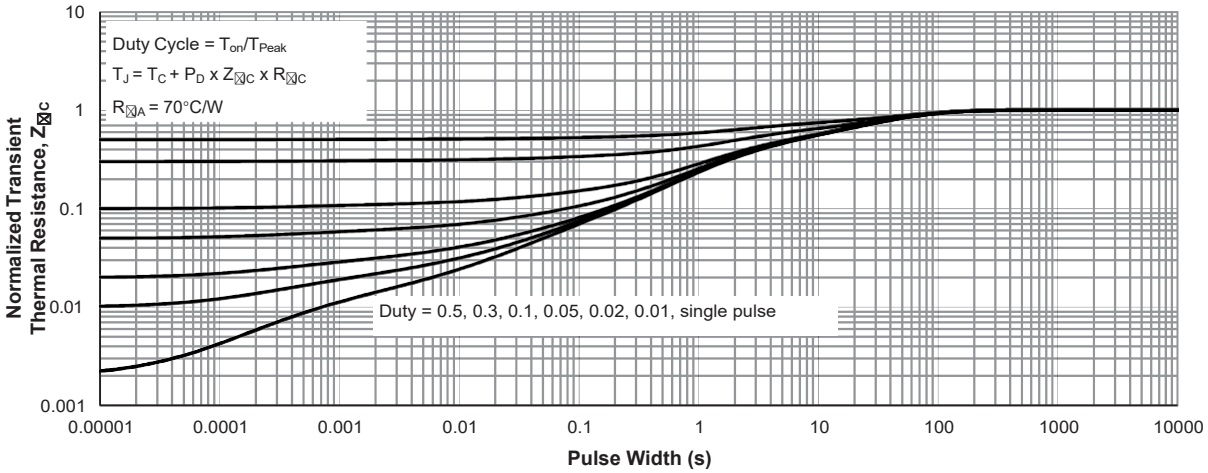


Figure 11: Normalized Maximum Transient Thermal Impedance